

Supporting online Materials for

**Oxygen-doped porous silicon carbide sphere as electrode material for
supercapacitors**

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1. N₂ adsorption-desorption isotherm and Pore-size distribution of MMPSiC

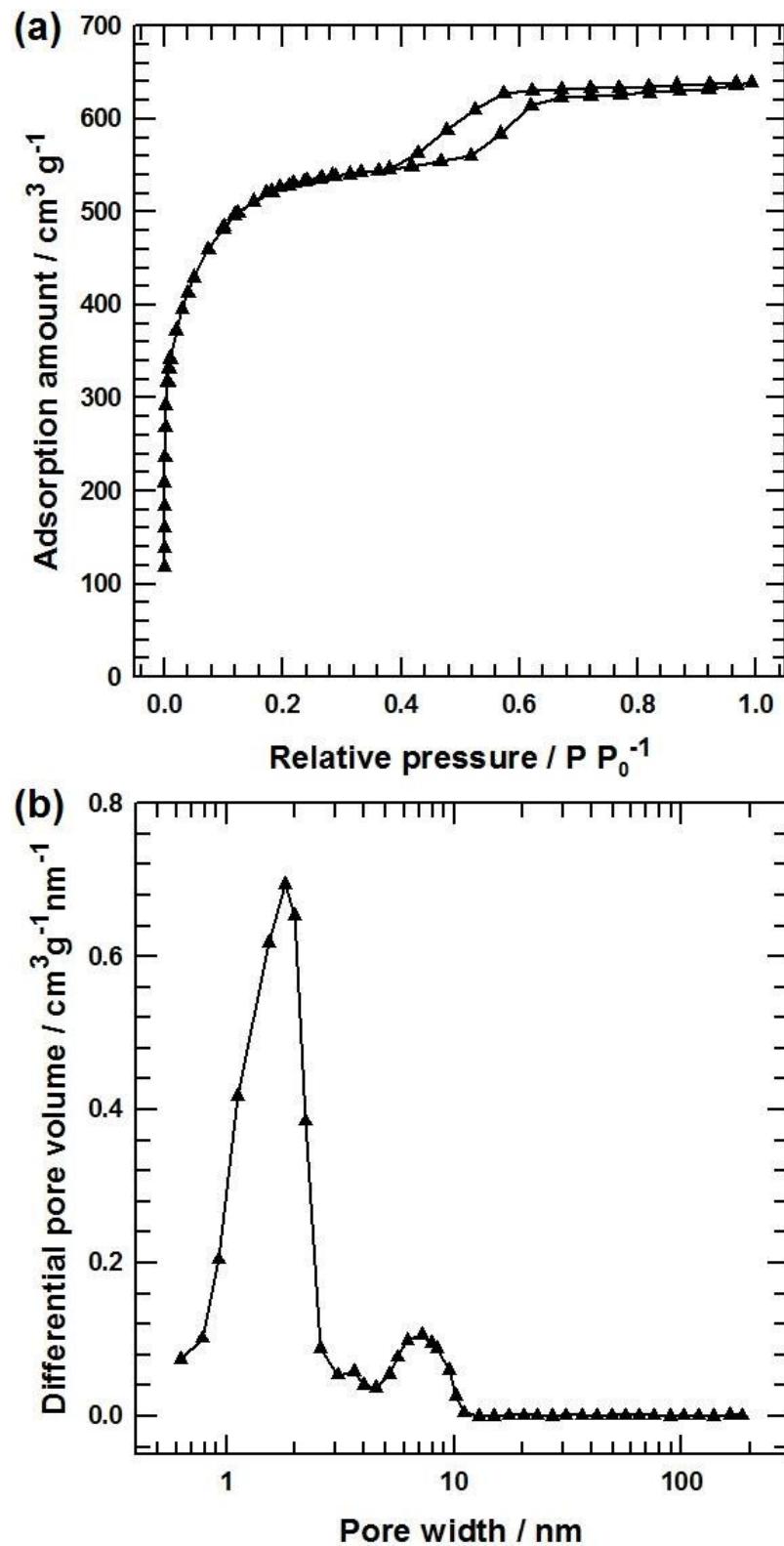


Figure S1. (a) Nitrogen adsorption-desorption isotherm of MMPSiC. (b) Pore-size distribution of MMPSiC.

2. N₂ adsorption-desorption isotherm and Pore-size distribution of OMMPSiC-20h

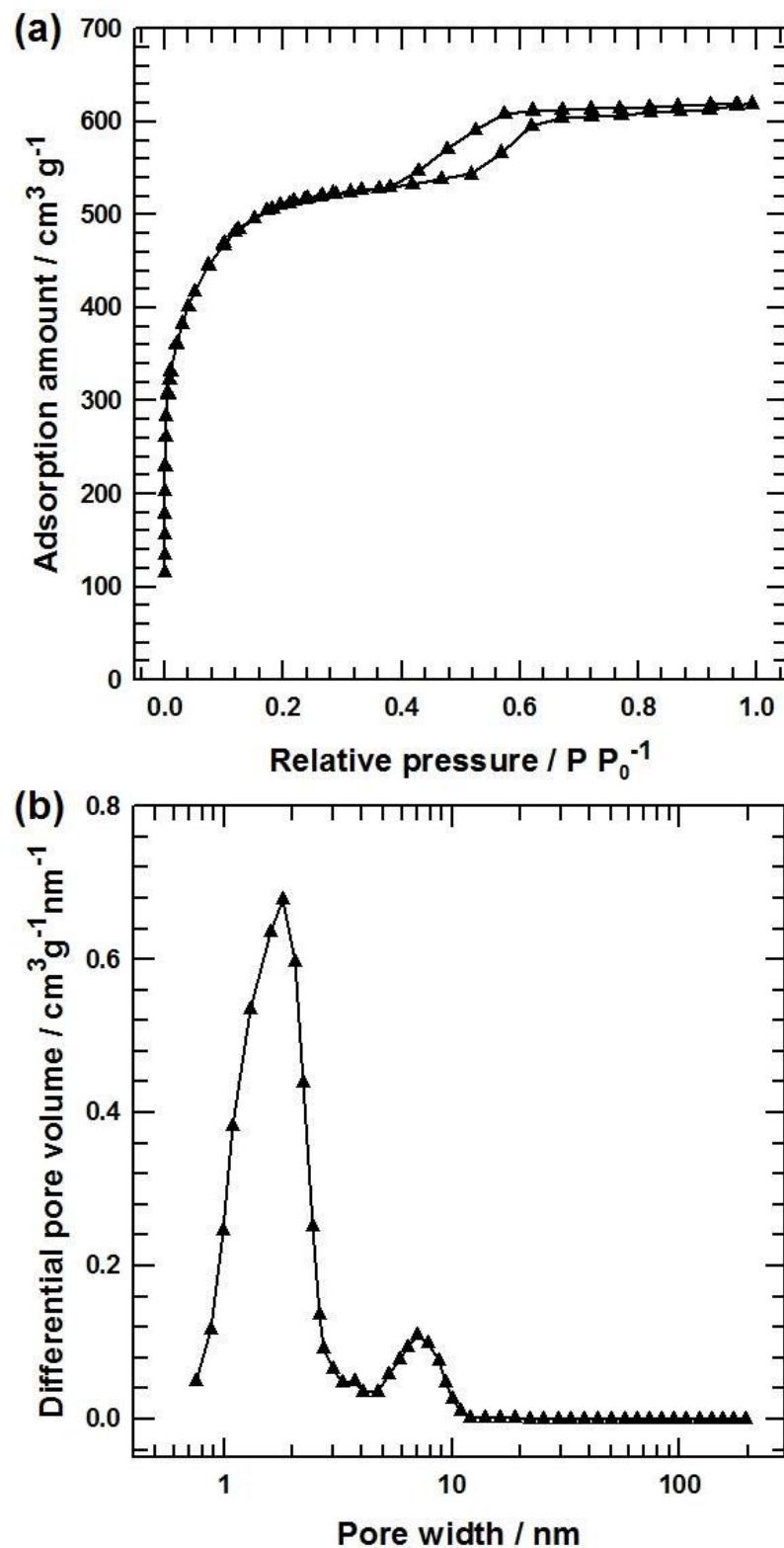


Figure S2. (a) Nitrogen adsorption-desorption isotherm of OMMPSiC-20h. (b) Pore-size distribution of OMMPSiC-20h.

3. N₂ adsorption-desorption isotherm and Pore-size distribution of OMMPSiC-24h

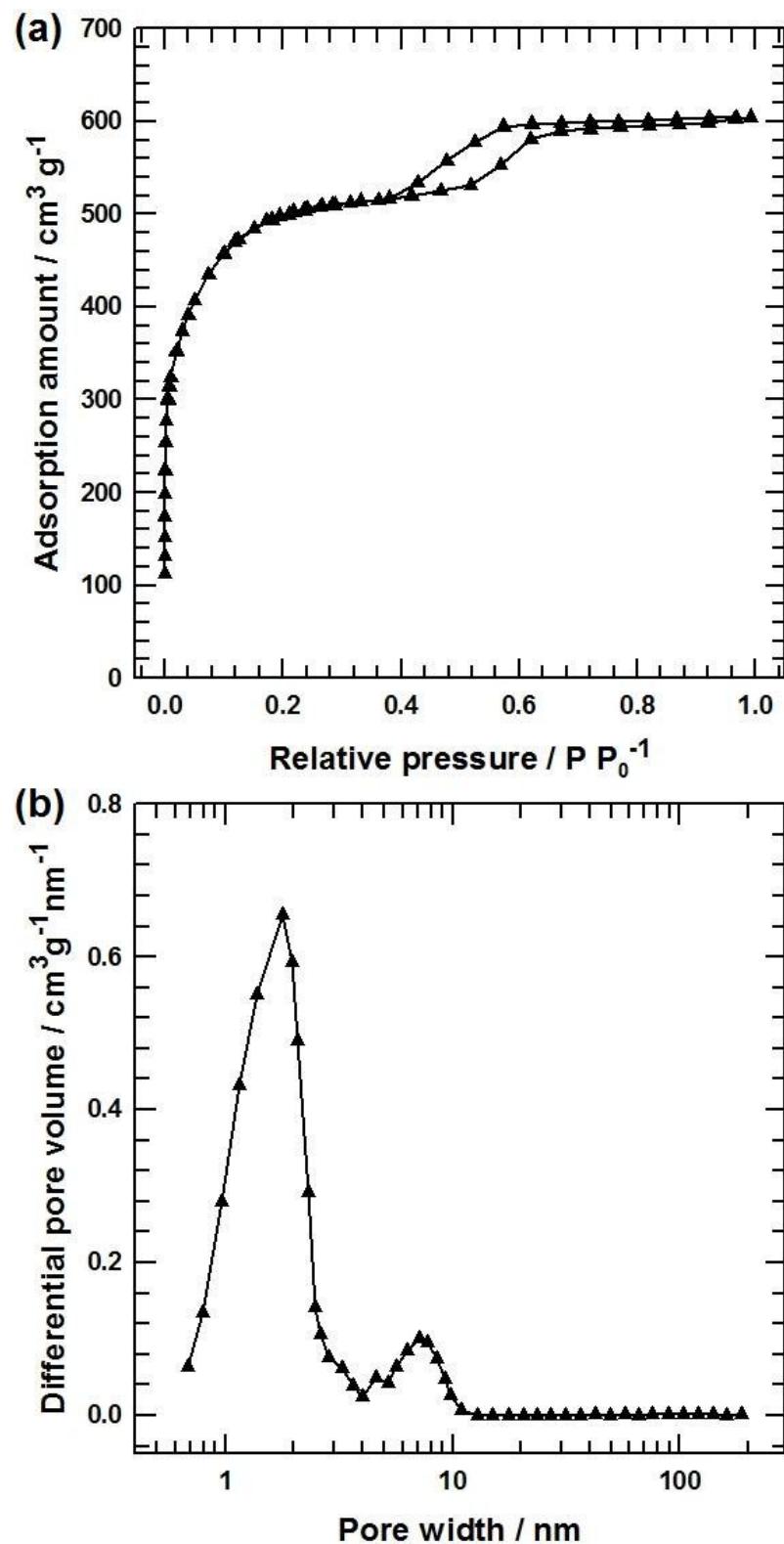


Figure S3. (a) Nitrogen adsorption-desorption isotherm of OMMPSiC-24h. (b) Pore-size distribution of OMMPSiC-24h.

4. N₂ adsorption-desorption isotherm and Pore-size distribution of OMMPSiC-28h

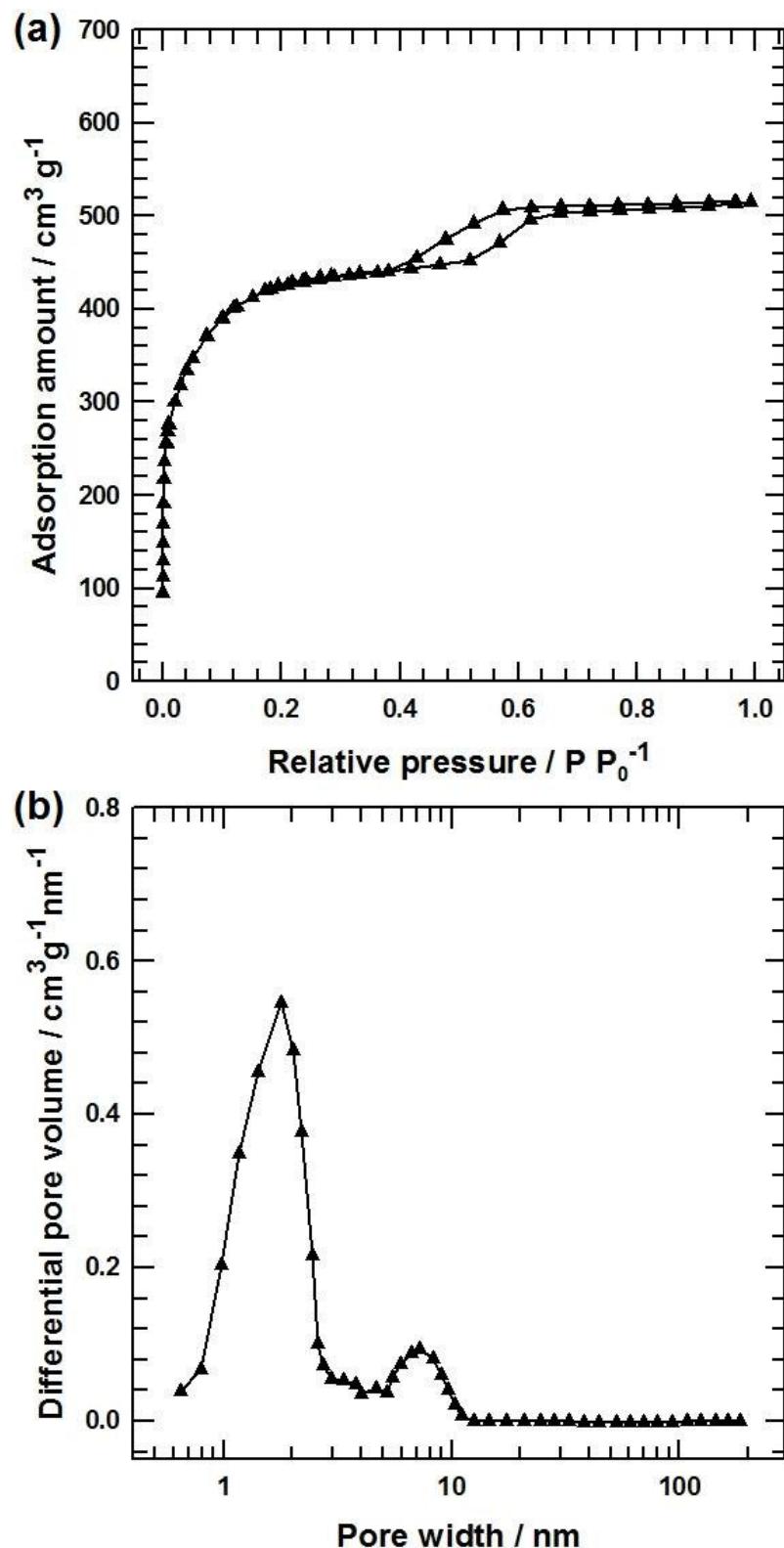


Figure S4. (a) Nitrogen adsorption-desorption isotherm of OMMPSiC-28h. (b) Pore-size distribution of OMMPSiC-28h.

5. N₂ adsorption-desorption isotherm and Pore-size distribution of OMMPSiC-32h

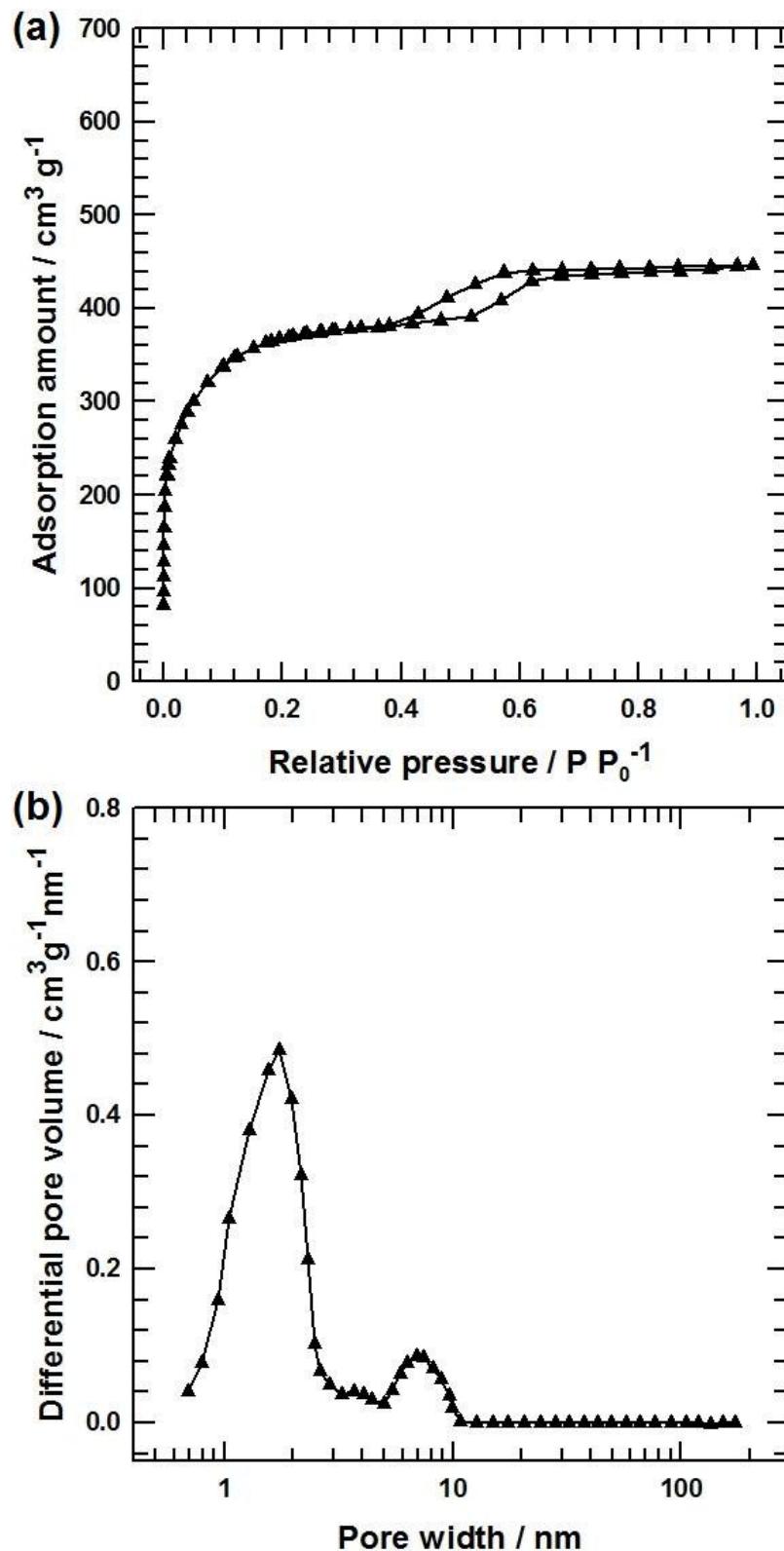


Figure S5. (a) Nitrogen adsorption-desorption isotherm of OMMPSiC-32h. (b) Pore-size distribution

of OMMPSiC-32h.

Table S1. The Si 2p peak position and the relative atomic percentages of various peaks in MMPSiC and OMMPSiC-*H*

Fitting of the Si 2p peak Binding energy [eV] (relative atomic percentage [%])					
	Si-C	SiOC ₃	SiO ₂ C ₂	SiO ₃ C	SiO ₂
MMPSiC	99.5 (70.88)	100.42 (14.45)	101.3 (8.45)	102.2 (6.22)	-
OMMPSiC-20h	99.5 (68.69)	100.43 (14.31)	101.29 (8.40)	102.2 (6.16)	102.92 (2.44)
OMMPSiC-24h	99.49 (67.81)	100.44 (14.54)	101.3 (8.54)	102.22 (6.22)	102.92 (2.89)
OMMPSiC-28h	99.49 (65.75)	100.42 (15.10)	101.3 (9.36)	102.21 (6.53)	102.92 (3.27)
OMMPSiC-32h	99.5 (64.36)	100.42 (15.74)	101.32 (9.78)	102.22 (6.48)	102.92 (3.64)

Table S2. The C 1s peak position and the relative atomic percentages of various peaks in MMPSiC and OMMPSiC-*H*

Fitting of the C 1s peak Binding energy [eV] (relative atomic percentage [%])				
	Si-C	SiO _x C _y	C-C	C-OH/C-O-C
MMPSiC	282.7 (60.87)	283.68 (24.69)	284.6 (14.43)	-
OMMPSiC-20h	282.71 (54.96)	283.71 (22.86)	284.62 (13.03)	285.73 (9.15)
OMMPSiC-24h	282.71 (51.62)	283.72 (22.06)	284.61 (12.24)	285.73 (14.08)
OMMPSiC-28h	282.7 (45.92)	283.71 (21.38)	284.59 (10.89)	285.73 (21.81)
OMMPSiC-32h	282.7 (42.91)	283.72 (21.06)	284.6 (10.17)	285.73 (25.86)

Table S3. Pore characteristics of MMPSiC and OMMPSiC-*H*

	S _{BET} [m ² g ⁻¹]	S _{micro} [m ² g ⁻¹]	S _{meso} [m ² g ⁻¹]	V _{tot} [cm ³ g ⁻¹]	V _{micro} [cm ³ g ⁻¹]	V _{meso} [cm ³ g ⁻¹]
MMPSiC	1713	1372	341	1.233	0.618	0.615
OMMPSiC-20h	1672	1346	326	1.19	0.603	0.587
OMMPSiC-24h	1625	1309	316	1.148	0.581	0.567
OMMPSiC-28h	1407	1102	305	1.031	0.485	0.546
OMMPSiC-32h	1274	983	291	0.948	0.429	0.519